PROCEEDINGS OF SPIE

Design-Process-Technology Co-optimization for Manufacturability XII

Jason P. Cain Chi-Min Yuan Editors

28 February–1 March 2018 San Jose, California, United States

Sponsored by SPIE

Cosponsored by Hitachi High Technologies, America, Inc. (United States)

Published by SPIE

Volume 10588

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Author(s), "Title of Paper," in *Design-Process-Technology Co-optimization for Manufacturability XII*, edited by Jason P. Cain, Chi-Min Yuan, Proceedings of SPIE Vol. 10588 (SPIE, Bellingham, WA, 2018) Seven-digit Article CID Number.

ISSN: 0277-786X

ISSN: 1996-756X (electronic)

ISBN: 9781510616684

ISBN: 9781510616691 (electronic)

Published by

SPIE

P.O. Box 10, Bellingham, Washington 98227-0010 USA Telephone +1 360 676 3290 (Pacific Time)· Fax +1 360 647 1445

SPIE.org

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Printed in the United States of America Vm7 i ffUb 5 qpc WUHY qz abWzi bXYf Wy bqY Zfca CD-9.

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